

Silicon PNP Power Transistors

2N5954 2N5955 2N5956

DESCRIPTION

- With TO-66 package
- Low collector saturation voltage
- Excellent safe operating area
- Complement to type 2N6372/6373/6374

APPLICATIONS

- Designed for driver circuits, switching and amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Fig.1 simplified outline (TO-66) and symbol

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2N5954	Open emitter	-90	V
		2N5955		-70	
		2N5956		-50	
V_{CEO}	Collector-emitter voltage	2N5954	Open base	-80	V
		2N5955		-60	
		2N5956		-40	
V_{EBO}	Emitter-base voltage		Open collector	-5	V
I_C	Collector current			-6	A
I_B	Base current			-2	A
P_D	Total Power Dissipation		$T_C = 25\square$	40	W
T_j	Junction temperature			150	$\square$
T_{stg}	Storage temperature			-65~200	$\square$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-c}$	Thermal resistance junction to case	4.3	$\square/W$

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CHARACTERISTICS

T_j=25℃ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	2N5954	I _C =-0.1A ; I _B =0	-80			V
		2N5955		-60			
		2N5956		-40			
V _{CEsat}	Collector-emitter saturation voltage	2N5954	I _C =-2A; I _B =-0.2A			-1.0	V
		2N5955	I _C =-2.5A; I _B =-0.25A				
		2N5956	I _C =-3A; I _B =-0.3A				
V _{BE-1}	Base-emitter on voltage	2N5954	I _C =-2A ; V _{CE} =-4V			-2.0	V
		2N5955	I _C =-2.5A ; V _{CE} =-4V				
		2N5956	I _C =-3A ; V _{CE} =-4V				
V _{BE-2}	Base-emitter on voltage		I _C =-6A ; V _{CE} =-4V			-3.0	V
I _{CEO}	Collector cut-off current	2N5954	V _{CE} =-65V; I _B =0			-1.0	mA
		2N5955	V _{CE} =-45V; I _B =0				
		2N5956	V _{CE} =-25V; I _B =0				
I _{CEV}	Collector cut-off current(R _{BE} =100Ω)		V _{CE} =Rated V _{CE} ; V _{BE(off)} =1.5V T _C =150℃			-0.1 -2.0	mA
I _{EBO}	Emitter cut-off current		V _{EB} =-5V; I _C =0			-0.1	mA
h _{FE-1}	DC current gain	2N5954	I _C =-2A ; V _{CE} =-4V	20		100	
		2N5955	I _C =-2.5A ; V _{CE} =-4V				
		2N5956	I _C =-3A ; V _{CE} =-4V				
h _{FE-2}	DC current gain		I _C =-6A ; V _{CE} =-4V	5			
f _T	Transition frequency		I _C =-1A; V _{CE} =-4V; f=1.0MHz	5			MHz

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PACKAGE OUTLINE

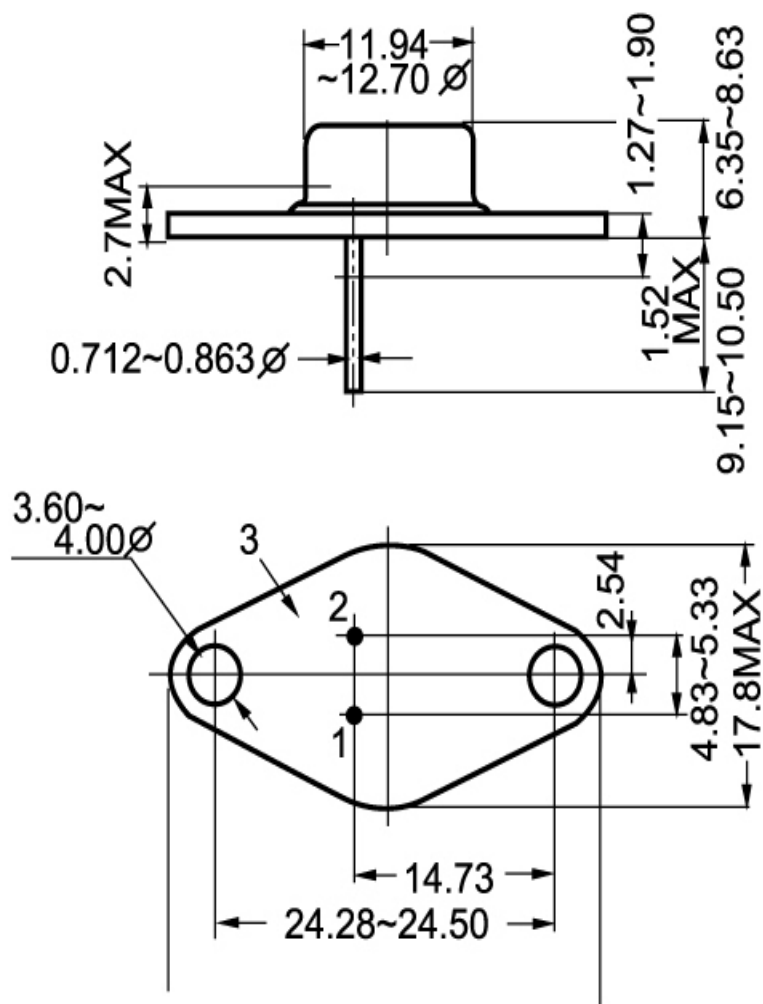


Fig.2 outline dimensions